

150V Depletion-Mode Power MOSFET

General Features

- Depletion Mode (Normally On)
- Proprietary Advanced Planar Technology
- Rugged Polysilicon Gate Cell Structure
- Fast Switching Speed
- RoHS Compliant
- Halogen-free Available

BV_{DSX}	$R_{DS(ON)} (Max.)$	$I_{DSS} (Min.)$
150V	25Ω	100mA

Applications

- New Energy Vehicles
- Industrial Automation
- Surge Protection
- Non-isolated Linear Power Supply
- Normally-on Switches
- Linear Amplifier
- Constant Current Source
- Telecom



Ordering Information

Part Number	Package	Marking	Remark
DMZ12C15A	SOT-23	12C15	Halogen Free

Absolute Maximum Ratings

$T_A=25^{\circ}C$ unless otherwise specified

Symbol	Parameter	DMZ12C15A	Unit
V_{DSX}	Drain-to-Source Voltage ^[1]	150	V
V_{DGX}	Drain-to-Gate Voltage ^[1]	150	V
I_D	Continuous Drain Current	0.1	A
I_{DM}	Pulsed Drain Current ^[2]	0.4	
P_D	Power Dissipation	0.50	W
V_{GS}	Gate-to-Source Voltage	±20	V
T_L	Soldering Temperature Distance of 1.6mm from case for 10 seconds	300	°C
T_J and T_{STG}	Operating and Storage Temperature Range	-55 to 150	

Caution: Stresses greater than those listed in the “Absolute Maximum Ratings” may cause permanent damage to the device.

Note: The MOSFET is sensitive to electrostatic discharge. When handling this device, the worktables, operators, soldering irons and other objects should be protected against anti-static discharge.

Thermal Characteristics

Symbol	Parameter	DMZ12C15A	Unit
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	250	K/W

Electrical Characteristics

OFF Characteristics

 $T_A=25^\circ\text{C}$ unless otherwise specified

Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Conditions
BV_{DSX}	Drain-to-Source Breakdown Voltage	150	--	--	V	$V_{GS}=-10\text{V}$, $I_D=250\mu\text{A}$
$I_{D(OFF)}$	Drain-to-Source Leakage Current	--	--	200	nA	$V_{DS}=150\text{V}$, $V_{GS}=-10\text{V}$
		--	--	100	μA	$V_{DS}=150\text{V}$, $V_{GS}=-10\text{V}$ $T_J=125^\circ\text{C}$
I_{GSS}	Gate-to-Source Leakage Current	--	--	± 100	nA	$V_{GS}=\pm 20\text{V}$, $V_{DS}=0\text{V}$

ON Characteristics

 $T_A=25^\circ\text{C}$ unless otherwise specified

Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Conditions
I_{DSS}	Saturated Drain-to-Source Current	100	--	--	mA	$V_{GS}=0\text{V}$, $V_{DS}=25\text{V}$
$R_{DS(ON)}$	Static Drain-to-Source On-Resistance	--	14	25	Ω	$V_{GS}=0\text{V}$, $I_D=50\text{mA}^{[3]}$
$V_{GS(OFF)}$	Gate-to-Source Cut-off Voltage	-2.5	--	-5.0	V	$V_{DS}=3\text{V}$, $I_D=8\mu\text{A}$
gfs	Forward Transconductance	--	85	--	mS	$V_{DS}=10\text{V}$, $I_D=50\text{mA}$

Dynamic Characteristics

Essentially independent of operating temperature

Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Conditions
C_{iss}	Input Capacitance	--	33.2	--	pF	$V_{GS}=-10\text{V}$ $V_{DS}=25\text{V}$ $f=1.0\text{MHz}$
C_{oss}	Output Capacitance	--	12.8	--		
C_{rss}	Reverse Transfer Capacitance	--	6.5	--		
Q_g	Total Gate Charge	--	1.1	--	nC	$V_{GS}=-10\text{V}\sim 5\text{V}$ $V_{DD}=25\text{V}$, $I_D=80\text{mA}$
Q_{gs}	Gate-to-Source Charge	--	0.6	--		
Q_{gd}	Gate-to-Drain (Miller) Charge	--	0.2	--		

Resistive Switching Characteristics

Essentially independent of operating temperature

Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Conditions
$t_{d(on)}$	Turn-on Delay Time	--	6.4	--	ns	$V_{GS}=-10\text{V}\sim 0\text{V}$ $V_{DD}=25\text{V}$, $I_D=80\text{mA}$ $R_G=10\Omega$
t_{rise}	Rise Time	--	4.8	--		
$t_{d(off)}$	Turn-off Delay Time	--	5.6	--		
t_{fall}	Fall Time	--	35.2	--		

Source-Drain Diode Characteristics

 $T_A=25^\circ\text{C}$ unless otherwise specified

Symbol	Parameter	Min.	Typ.	Max.	Units	Test Conditions
V_{SD}	Diode Forward Voltage	--	--	1.2	V	$I_{SD}=50\text{mA}$, $V_{GS}=-10\text{V}$

NOTE:

[1] $T_J=+25^\circ\text{C}$ to $+150^\circ\text{C}$.

[2] Repetitive rating, pulse width limited by maximum junction temperature.

[3] Pulse width $\leq 380\mu\text{s}$; duty cycle $\leq 2\%$.

Typical Characteristics

Figure 1. Maximum Power Dissipation vs. Case Temperature

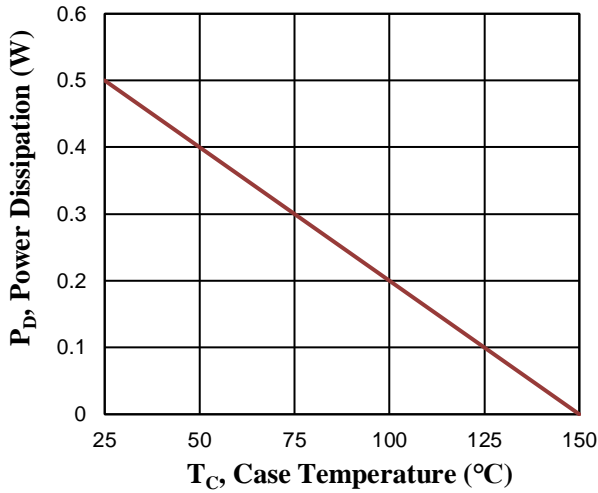


Figure 2. Maximum Continuous Drain Current vs. Case Temperature

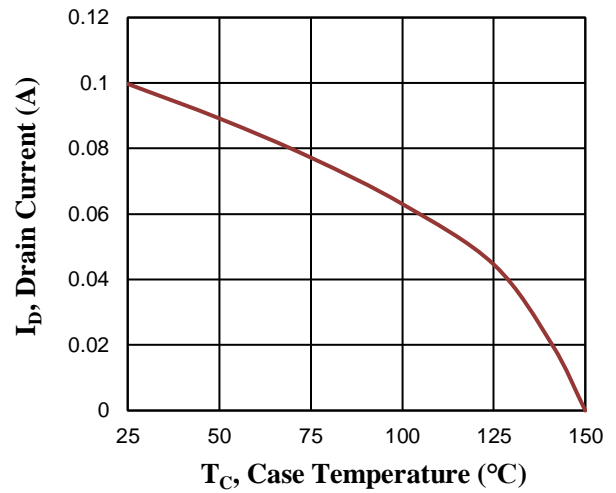


Figure 3. Typical Output Characteristics

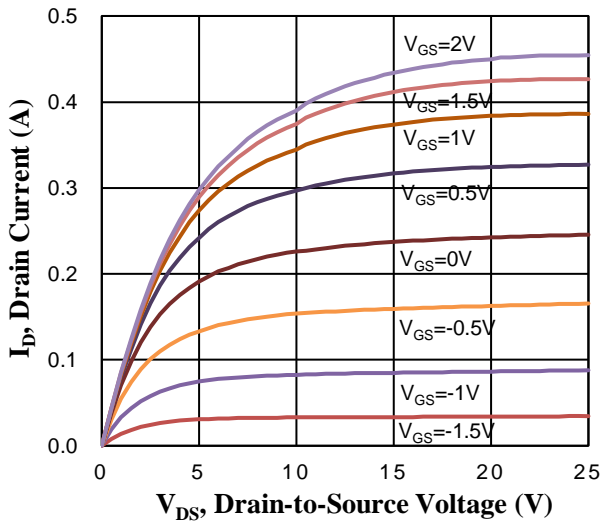


Figure 4. Typical Transfer Characteristics

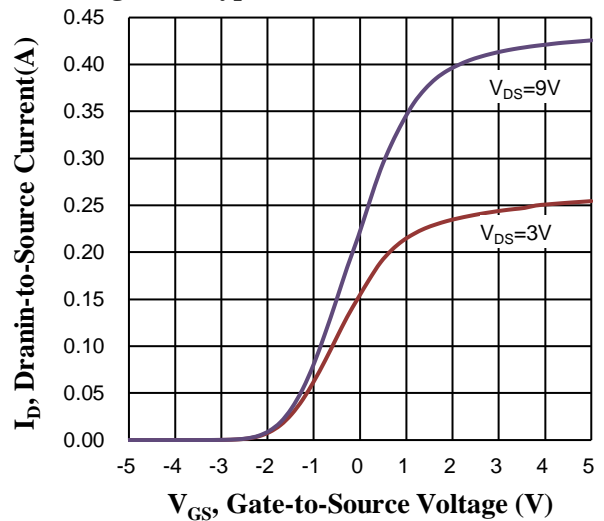


Figure 5. Typical Capacitance vs. Drain-to-Source Voltage

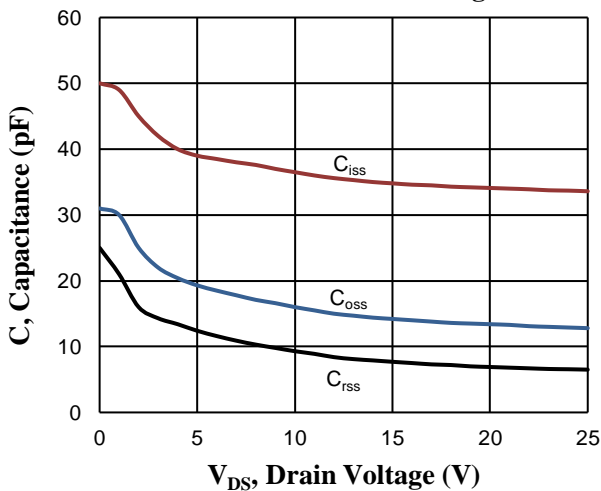
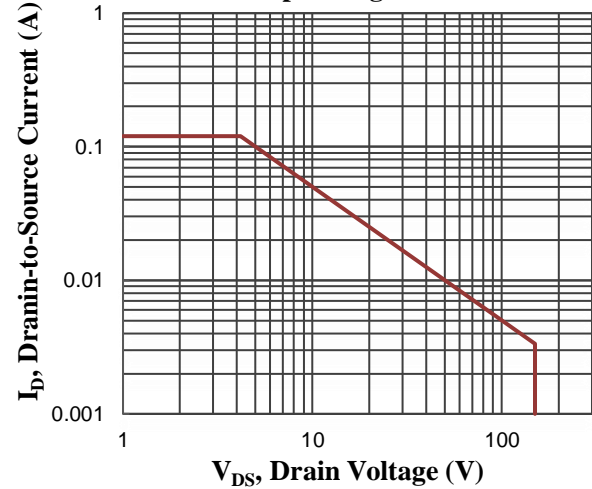
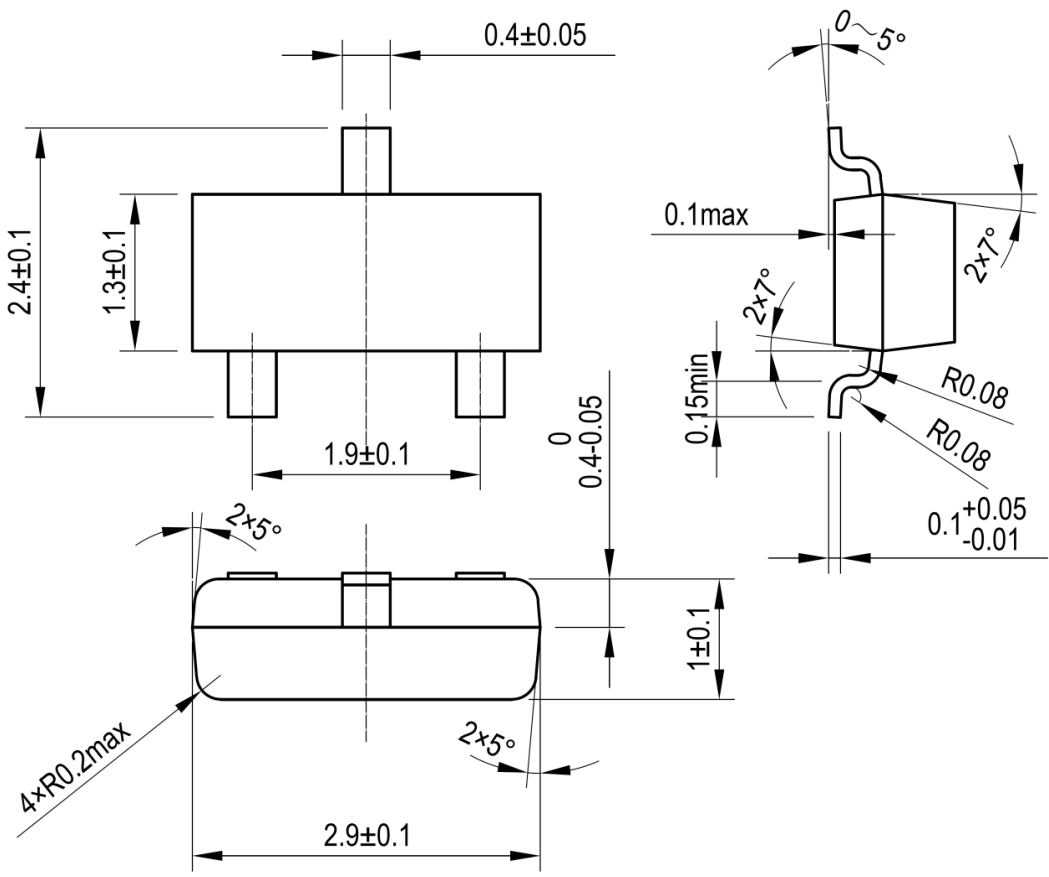


Figure 6. Maximum Forward Safe Operating Area



Package Dimensions

SOT-23



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ARK Microelectronics Co., Ltd.
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